

DECLARATION AND POWER OF ATTORNEY

As a below named inventor, I hereby declare that:

My residence, post office address, and citizenship are as stated below next to my name,

I believe I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter claimed and for which a patent is sought on the invention entitled:

LATERAL HETEROJUNCTION BIPOLAR TRANSISTOR AND METHOD OF MANUFACTURE USING SELECTIVE EPITAXIAL GROWTH

the specification of which

☒ is attached hereto

☐ was filed on ____ as Application Serial No. ____ and was amended on ____ (if applicable).

I hereby state that I have reviewed and understand the contents of the above-identified specification, including the claims, as amended by any amendment referred to above.

I do not know and do not believe the same was ever known or used in the United States of America before this invention thereof or more than one year prior to this application, and that the same was not in public use or on sale in the United States of America more than one year prior to this application. I acknowledge the duty to disclose information which is known to me to be material to patentability in accordance with title 37, Code of Federal Regulations, section 1.56.

I hereby claim foreign priority benefits under Title 35, United States Code, Section 119(a)-(d) or Section 365(b) of any foreign application(s) for patent or inventor's certificate, or Section 365(a) of any PCT international application which designated at least one country other than the United States, listed below and have also identified below any foreign application for patent or inventor's certificate having a filing date before that of the application on which priority is claimed:

Prior Foreign Application(s):

<u>Number</u>	<u>Country</u>	<u>Day/Month/Year filed</u>	<u>Priority Claimed</u>	
			<u>Yes</u>	<u>No</u>

I hereby claim the benefit under 35 USC 119(e) of any United States provisional application(s) listed below:

Prior Provisional Application(s):

<u>Application Number</u>	<u>Filing Date</u>
---------------------------	--------------------

I hereby claim the benefit under Title 35, United States Code, Section 120 of any United States application(s), or Section 365(c) of any PCT international application designating the United States, listed below and, insofar as the subject matter of each of the claims of this application is not disclosed in the prior United States or PCT international application in the manner provided by the first paragraph of Title 35, United States Code, Section 112, I acknowledge the duty to disclose material information as defined in Title 37, Code of Federal

Regulations, Section 1.56 which occurred between the filing date of the prior application and the national or PCT international filing date of this application:

Prior U.S. Application(s):

<u>Serial No.</u>	<u>Filing Date</u>	<u>Status: Patented, Pending, Abandoned</u>
-------------------	--------------------	---

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

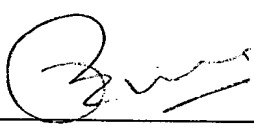
I hereby revoke any previous Powers of Attorney and appoint the following attorney(s) and/or agent(s), each said individual being a member or associate of The Law Offices of Mikio Ishimaru or being employed by Chartered Semiconductor Manufacturing Ltd.:

Mikio Ishimaru	Reg. No. 27,449	William D. Zahrt II	Reg. No. 26,070
----------------	-----------------	---------------------	-----------------

for so long as they remain with such law offices or company with full power of substitution and revocation, to prosecute this application and to transact in connection therewith all business in the Patent and Trademark Office and before competent International Authorities; said appointment to be to the exclusion of myself and my other attorney(s); and all future correspondence should be addressed to:

Mikio Ishimaru
The Law Offices of Mikio Ishimaru
1110 Sunnyvale – Saratoga Rd., Suite A1
Sunnyvale, California 94087

.....


Inventor's signature:  Date: 12/11/03

Full name of sole or first inventor: Purakh Raj Verma

Citizenship: India

Residence Address, including country: Blk #345, Apt #11-204
St #32, Woodlands
Singapore 730345
Singapore

P.O. Address: c/o Chartered Semiconductor Manufacturing Ltd.
60 Woodlands Industrial Park D.
Street 2
Singapore 738406

Inventor's signature:  Date: 13/11/03

Full name of joint inventor: Shao-fu Sanford Chu

Citizenship: U.S.A.

Residence Address, including
country: 9 Beechwood Grove
Singapore, 737927
Singapore

Post Office Address: c/o Chartered Semiconductor Manufacturing Ltd.
60 Woodlands Industrial Park D.
Street 2
Singapore 738406


Inventor's signature: Lap Chan Date: Nov 13, 03

Full name of joint inventor: Lap Chan

Citizenship: U.S.A.

Residence Address, including
country: 3 Pine Grove #9-02 Astor Green
Singapore, 597590
Singapore

Post Office Address: c/o Chartered Semiconductor Manufacturing Ltd.
60 Woodlands Industrial Park D.
Street 2
Singapore 738406

Inventor's signature:  Date: 2003.10.30

Full name of joint inventor: Jia Zhen Zheng

Citizenship: Singapore

Residence Address, including
country: 38 Verde Grove

Singapore, 688570

Singapore

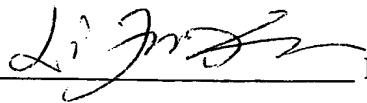
P.O. Address: c/o Chartered Semiconductor Manufacturing Ltd.

60 Woodlands Industrial Park D.

Street 2

Singapore 738406

Inventor's signature: _____



Date: _____

Nov 17th, 2003

Full name of joint inventor:

Jian Xun Li

Citizenship:

Republic of China

Residence Address, including
country:

BLK # 715 - Apt # 10-14D

Woodlands Drive-70

Singapore 730715

Singapore

P.O. Address:

c/o Chartered Semiconductor Manufacturing Ltd.

60 Woodlands Industrial Park D.

Street 2

Singapore 738406